


Thyristor/Diode (Super MAGN-A-PAK Power Modules), 570 A



Super MAGN-A-PAK

FEATURES

- High current capability
- High surge capability
- Industrial standard package
- 3000 V_{RMS} isolating voltage with non-toxic substrate
- Designed and qualified for industrial level
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

TYPICAL APPLICATIONS

- Motor starters
- DC motor controls - AC motor controls
- Uninterruptible power supplies

PRIMARY CHARACTERISTICS

| | |
|-------------|---------------------------|
| $I_{T(AV)}$ | 570 A |
| Type | Modules - thyristor/diode |
| Package | Super MAGN-A-PAK |

MAJOR RATINGS AND CHARACTERISTICS

| SYMBOL | CHARACTERISTICS | VALUES | UNITS |
|------------------------|------------------------------------|-------------|----------------------------|
| $I_{T(AV)}, I_{F(AV)}$ | $T_C = 74\text{ }^{\circ}\text{C}$ | 570 | A |
| $I_{T(RMS)}$ | $T_C = 74\text{ }^{\circ}\text{C}$ | 895 | |
| I_{TSM} | 50 Hz | 17 800 | |
| | 60 Hz | 18 700 | |
| I^2t | 50 Hz | 1591 | kA ² s |
| | 60 Hz | 1452 | |
| $I^2\sqrt{t}$ | | 15 910 | kA ² \sqrt{s} |
| V_{RRM} | Range | 1800 | V |
| T_{Stg} | Range | -40 to +135 | $^{\circ}\text{C}$ |
| T_J | Range | -40 to +135 | |

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

| TYPE NUMBER | VOLTAGE CODE | V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V | V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | I_{RRM}/I_{DRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA |
|------------------|--------------|--|--|--|
| VS-VSKH570-18PbF | 18 | 1800 | 1900 | 120 |



| ON-STATE CONDUCTION | | | | | | |
|--|----------------------------|---|---------------------------|---|--------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS |
| Maximum average on-state current at case temperature | $I_{T(AV)}$ $I_{F(AV)}$ | 180° conduction, half sine wave | | | 570 | A |
| | | | | | 74 | °C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | 180° conduction, half sine wave at $T_C = 74\text{ °C}$ | | | 895 | A |
| Maximum peak, one-cycle, non-repetitive on-state surge current | I_{TSM} , I_{FSM} | t = 10 ms | No voltage reapplied | Sinusoidal half wave, initial $T_J = T_J$ maximum | 17.8 | kA |
| | | t = 8.3 ms | | | 18.7 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | | 15.0 | |
| | | t = 8.3 ms | | | 15.7 | |
| Maximum I^2t for fusing | I^2t | t = 10 ms | No voltage reapplied | | 1591 | kA ² s |
| | | t = 8.3 ms | | | 1452 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | | 1125 | |
| | | t = 8.3 ms | | | 1027 | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 ms to 10 ms, no voltage reapplied | | | 15 910 | kA ² /√s |
| Low level value or threshold voltage | $V_{T(TO)1}$ | (16.7 % × π × $I_{T(AV)}$ < I < π × $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.864 | V |
| High level value of threshold voltage | $V_{T(TO)2}$ | (I > π × $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.97 | |
| Low level value on-state slope resistance | r_{t1} | (16.7 % × π × $I_{T(AV)}$ < I < π × $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.411 | mΩ |
| High level value on-state slope resistance | r_{t2} | (I > π × $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.362 | |
| Maximum on-state voltage drop | SCR V_{TM} | $I_{pk} = 1500\text{ A}$, $T_J = 25\text{ °C}$, $t_p = 10\text{ ms}$ sine pulse | | | 1.50 | V |
| | Diode V_{FM} | | | | | |
| Maximum holding current | I_H | $T_J = 25\text{ °C}$, anode supply 12 V resistive load | | | 500 | mA |
| Maximum latching current | I_L | | | | 1000 | |

| SWITCHING | | | | | |
|---|---------|--|--|--|----------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES UNITS |
| Maximum rate of rise of turned-on current | di/dt | $T_J = T_J$ maximum, $I_{TM} = 400\text{ A}$, V_{DRM} applied | | | 1000 $A/\mu s$ |
| Typical delay time | t_d | Gate current 1 A, $di_g/dt = 1\text{ A}/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25\text{ °C}$ | | | 2.0 μs |
| Typical turn-off time | t_q | $I_{TM} = 750\text{ A}$; $T_J = T_J$ maximum, $di/dt = -60\text{ A}/\mu s$, $V_R = 50\text{ V}$, $dV/dt = 20\text{ V}/\mu s$, gate 0 V 100 Ω | | | 200 |

| BLOCKING | | | | | |
|--|--------------------------|--|--|--|----------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum, linear to $V_D = 80\% V_{DRM}$ | | | 1000 $V/\mu s$ |
| RMS insulation voltage | V_{INS} | t = 1 s | | | 3000 V |
| Maximum peak reverse and off-state leakage current | I_{RRM} , I_{DRM} | $T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied | | | 120 mA |

**TRIGGERING**

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|---|-------------|--|--------|-------|
| Maximum peak gate power | P_{GM} | $T_J = T_J$ maximum, $t_p \leq 5$ ms | 10 | W |
| Maximum peak average gate power | $P_{G(AV)}$ | $T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$ | 2.0 | |
| Maximum peak positive gate current | $+I_{GM}$ | $T_J = T_J$ maximum, $t_p \leq 5$ ms | 3.0 | A |
| Maximum peak positive gate voltage | $+V_{GM}$ | | 20 | |
| Maximum peak negative gate voltage | $-V_{GM}$ | | 5.0 | |
| Maximum DC gate current required to trigger | I_{GT} | $T_J = 25$ °C, V_{ak} 12 V | 200 | mA |
| DC gate voltage required to trigger | V_{GT} | | 3.0 | |
| DC gate current not to trigger | I_{GD} | $T_J = T_J$ maximum | 10 | mA |
| DC gate voltage not to trigger | V_{GD} | | 0.25 | V |

THERMAL AND MECHANICAL SPECIFICATIONS

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
|---|--|---|------------------|-------|
| Maximum junction operating temperature range | T_J | | -40 to +135 | °C |
| Maximum storage temperature range | T_{Stg} | | -40 to +135 | |
| Maximum thermal resistance, junction to case per junction | R_{thJC} | DC operation | 0.065 | K/W |
| Maximum thermal resistance, case to heatsink | R_{thC-hs} | | 0.02 | |
| Mounting torque ± 10 % | Super MAGN-A-PAK to heatsink busbar to super MAGN-A-PAK | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound | 6 to 8 | Nm |
| | | | 12 to 15 | |
| Approximate weight | | | 1500 | g |
| Case style | | See dimensions (link at the end of datasheet) | Super MAGN-A-PAK | |

 ΔR_{thJC} CONDUCTION

| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS | UNITS |
|------------------|-----------------------|------------------------|---------------------|-------|
| 180° | 0.009 | 0.006 | $T_J = T_J$ maximum | K/W |
| 120° | 0.011 | 0.011 | | |
| 90° | 0.014 | 0.015 | | |
| 60° | 0.021 | 0.022 | | |
| 30° | 0.037 | 0.038 | | |

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

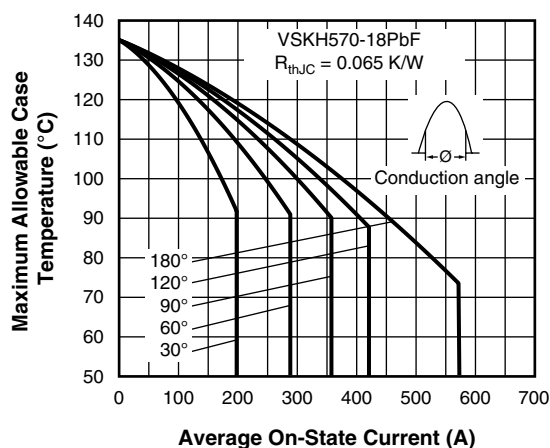


Fig. 1 - Current Ratings Characteristics

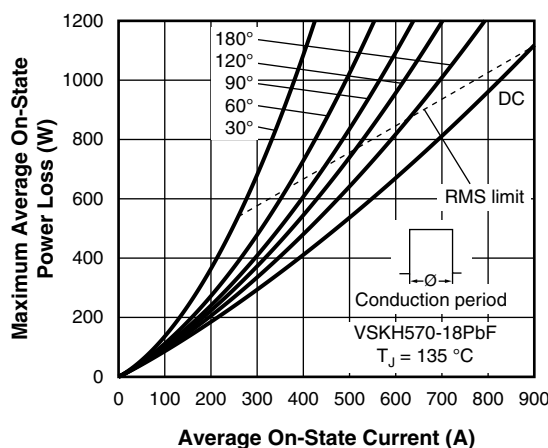


Fig. 4 - On-State Power Loss Characteristics

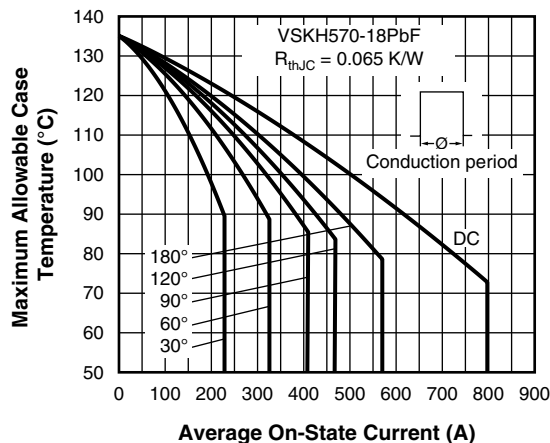


Fig. 2 - Current Ratings Characteristics

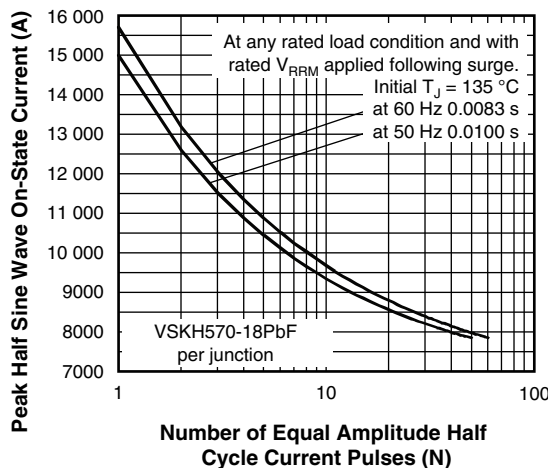


Fig. 5 - Maximum Non-Repetitive Surge Current

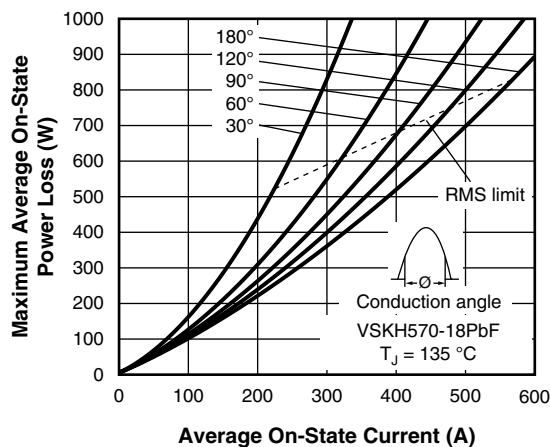


Fig. 3 - On-State Power Loss Characteristics

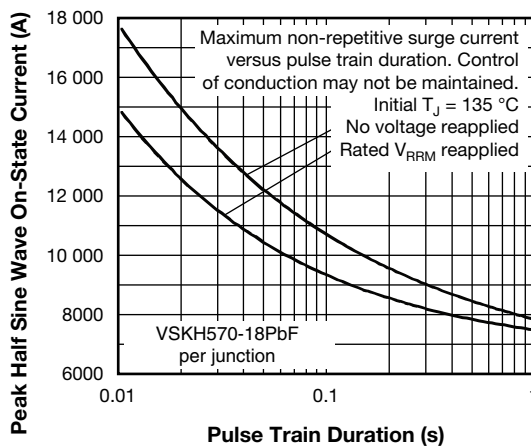


Fig. 6 - Maximum Non-Repetitive Surge Current

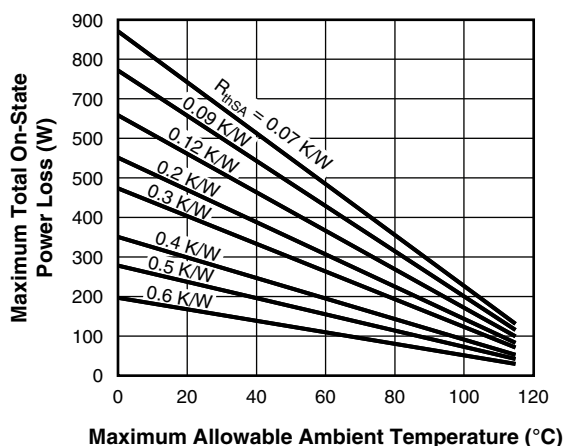
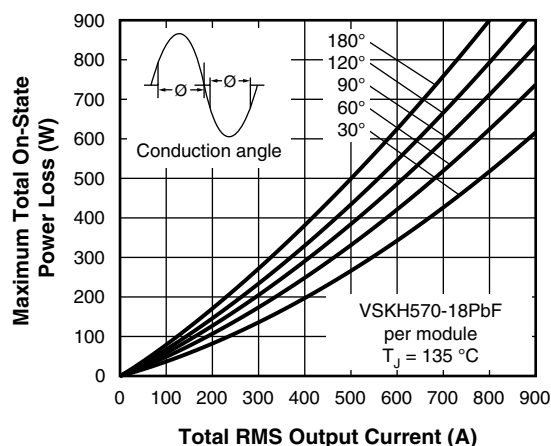


Fig. 7 - On-State Power Loss Characteristics

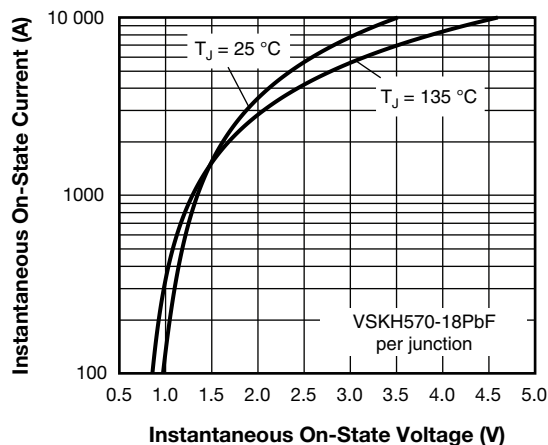


Fig. 8 - On-State Voltage Drop Characteristics

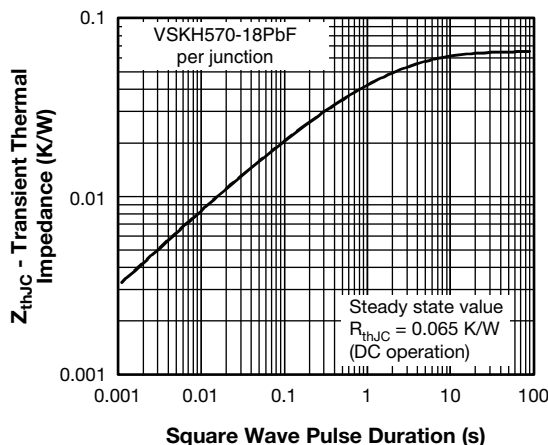
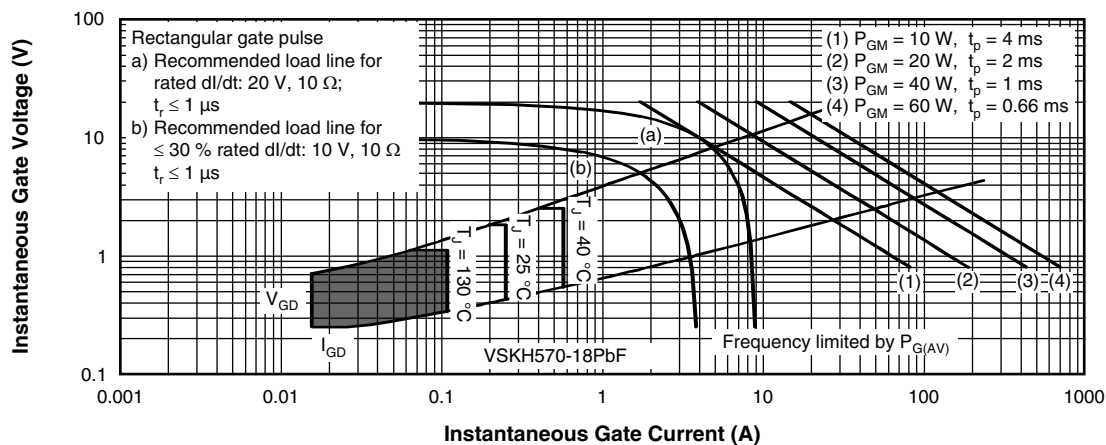
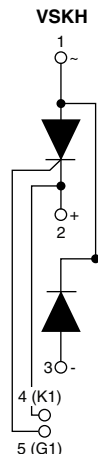

Fig. 9 - Thermal Impedance Z_{thJC} Characteristics


Fig. 10 - Gate Characteristics



ORDERING INFORMATION TABLE

| Device code | VS-VS | KH | 570 | - | 18 | PbF |
|-------------|-------------------------------------|----|-----|---|----|-----|
| | 1 | 2 | 3 | | 4 | 5 |
| 1 | - Vishay Semiconductors product | | | | | |
| 2 | - Circuit configuration (see below) | | | | | |
| 3 | - Current rating | | | | | |
| 4 | - Voltage code x 100 = V_{RRM} | | | | | |
| 5 | - Lead (Pb)-free | | | | | |

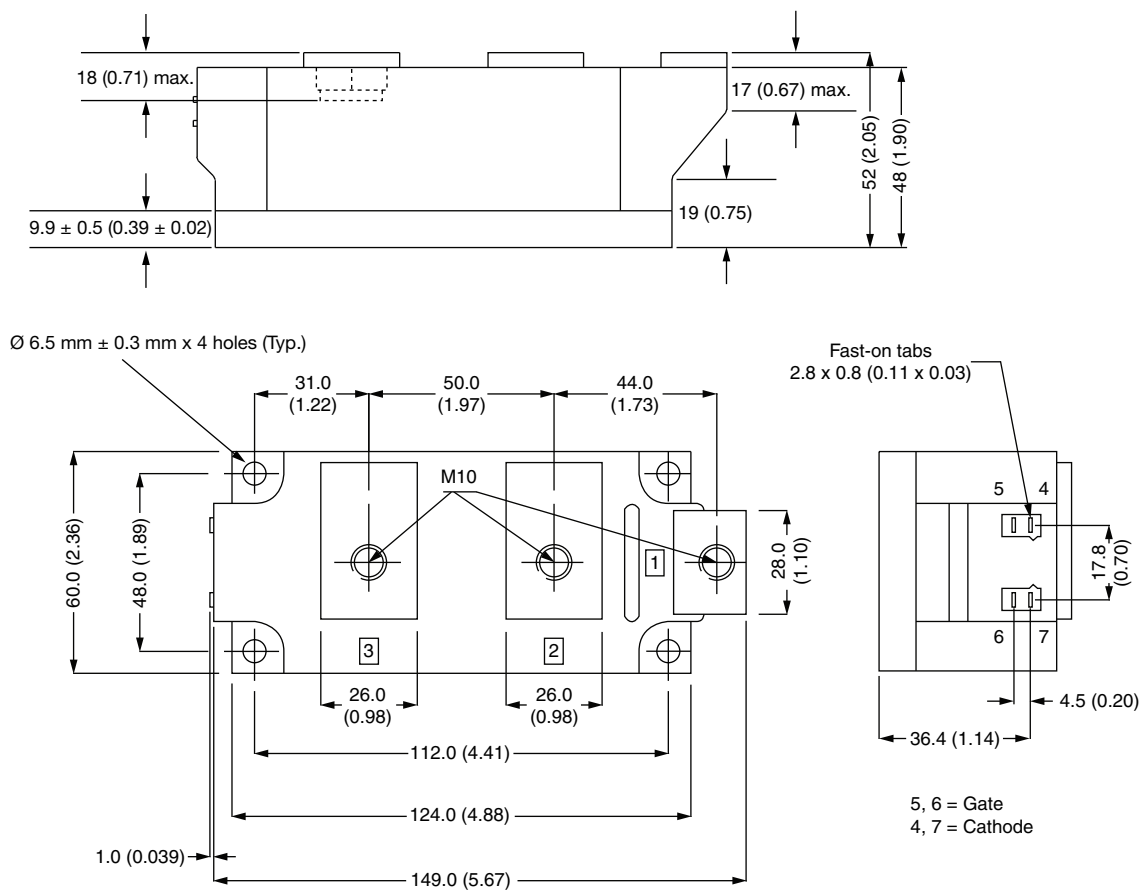
| CIRCUIT CONFIGURATION | | |
|---------------------------|----------------------------|--|
| CIRCUIT DESCRIPTION | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING |
| SCR/diode doubler circuit | KH |  |

| LINKS TO RELATED DOCUMENTS | |
|----------------------------|--|
| Dimensions | www.vishay.com/doc?95283 |



Super MAGN-A-PAK Thyristor/Diode

DIMENSIONS in millimeters (inches)





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